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EXAS ISTRUMENTS

Data sheet acquired from Harris Semiconductor SCHS263

CD74FCT653, CD74FCT654

January 1997

Features

Buffered Inputs

CD74FCT653

- Inverting

CD74FCT654

Non-Inverting

Circuit Design

• Typical Propagation Delay:

Speed of Bipolar FAST™/AS/S

Controlled Output Edge Rates

Input/Output Isolation to V_{CC}

Ordering Information

PART NUMBER

• 64mA Output Sink Current

6.8ns at $V_{CC} = 5V$, $T_A = 25^{\circ}C$, $C_I = 50pF$

SCR Latchup Resistant BiCMOS Process and

Output Voltage Swing Limited to 3.7V at V_{CC} = 5V

BiCMOS Technology with Low Quiescent Power

TEMP.

RANGE (°C)

FCT Interface Logic, Octal Bus Transceivers/ Registers, Open Drain (A Side), Three-State (B Side) NOT RECOMMENDED

Description

FOR NEW DESIGNS

Use CMOS Technology

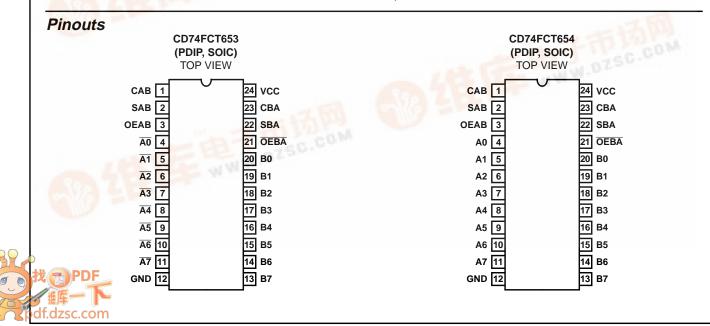
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PACKAGE

The CD74FCT653 and CD74FCT654 octal bus transceivers/registers use a small geometry BiCMOS technology. The output stage is a combination of bipolar and CMOS transistors that limits the output HIGH level to two diode drops below V_{CC}. This resultant lowering of output swing (OV to 3.7V) reduces power bus ringing (a source of EMI) and minimizes V_{CC} bounce and ground bounce and their effects during simultaneous output switching. The output configuration also enhances switching speed and is capable of sinking 64mA.

The CD74FCT653 is an inverting type having open drains on the A output and three state outputs on the B side. The CD74FCT654 differs only in that it is a noninverting type. These devices consist of bus transceiver circuits, D-Type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. Output Enables OEAB and OEBA are provided to control the transceiver functions. SAB and SBA control pins are provided to select whether real-time or stored data is transferred. The circuitry used for select control will eliminate the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A LOW input level selects real-time data and a HIGH selects stored data. The following examples demonstrate the four fundamental bus management functions that can be performed with the octal bus transceivers and registers.

Data on the A or B data bus, or both, can be stored in the internal D flip-flops by low to high transitions at the appropriate clock pins (CAB or CBA) regardless of the select or enable control pins. When SAB and SBA are in the real-time transfer mode, it is also possible to store data without using the internal D-Type flip-flops by simultaneously enabling OEAB and OEBA. In this configuration, each output reinforces its input. Thus, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines will remain at its last state.



PKG.

NO.

E24.3

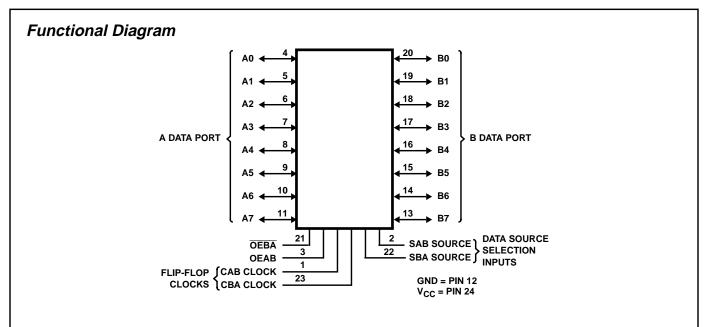
CD74FCT653EN 0 to 70 24 Ld PDIP

CD74FCT654EN 0 to 70 24 Ld PDIP E24.3 CD74FCT653M 0 to 70 24 Ld SOIC M24.3 CD74FCT654M 0 to 70 24 Ld SOIC M24.3

NOTE: When ordering the suffix M packages, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.



Data sheet acquired from Harris Semiconductor SCHS263



TRUTH TABLE

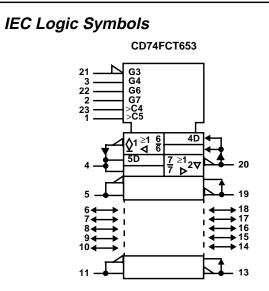
		INP	UTS			DAT	A I/O	OPERATION (OR FUNCTION
OEAB	OEBA	CAB	CBA	SAB	SBA	A0 THRU A7	B0 THRU B7	CD74FCT653	CD74FCT654
L	H	H or L	H or L	X	X	Input	Input	Isolation (Note 1)	Isolation (Note 1)
	H	↑	↑	X	X	Input	Input	Store A and B Data	Store A and B Data
X	H	↑	H or L	X	X	Input	Unspecified (2)	Store A, Hold B	Store A, Hold B
H	H	↑	↑	X (3)	X	Input	Output	Store A in both registers	Store A in both registers
L	X L	H or L ↑	$\uparrow \\ \uparrow$	X X	X X (3)	Unspecified (2) Output	Input Input	Hold A, Store B Store B in both registers	Hold A, Store B Store B in both registers
L	L	X	X	X	L	Output	Input	Real-Time \overline{B} Data to A Bus	Real-Time B Data to A Bus
	L	X	H or L	X	H	Output	Input	Stored \overline{B} Data to A Bus	Stored B Data to A Bus
H	H	X	X	L	X	Input	Output	Real-Time \overline{A} Data to B Bus	Real-Time A Data to B Bus
H	H	H or L	X	H	X	Input	Output	Stored \overline{A} Data to B Bus	Stored A Data to B Bus
Н	L	H or L	H or L	Н	Н	Output	Output	Stored \overline{A} Data to B Bus Stored \overline{B} Data to A Bus	Stored A Data to B Bus Stored B Data to A Bus

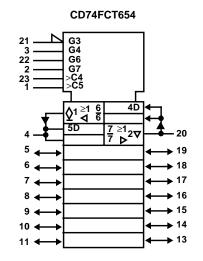
NOTES:

1. To prevent excess currents in the High-Z (isolation) modes, all I/O terminals should be terminated with $10k\Omega$ to $1M\Omega$ resistors.

2. The data output functions may be enabled or disabled by various signals at the OEAB or OEBA inputs. Data input functions are always enabled, i.e., data at the bus pins will be stored on every low-to-high transition on the clock inputs.

3. Select control = L; clocks can occur simultaneously. Select control = H; clocks must be staggered in order to load both registers.





Absolute Maximum Ratings

DC Supply Voltage (V _{CC})0.5	5V to 6V
DC Diode Current, I _{IK} (For V _I < -0.5V)	-20mA
DC Output Diode Current, I _{OK} (for V _O < -0.5V)	50mA
DC Output Sink Current per Output Pin, IO	70mA
DC Output Source Current per Output Pin, IO	-30mA
DC V _{CC} Current (I _{CC})	.140mA
DC Ground Current (I _{GND})	.528mA

Operating Conditions

Operating Temperature Range, T _A	0°C to 70°C
Supply Voltage Range, V _{CC}	
DC Input Voltage, V ₁	0 to V _{CC}
DC Output Voltage, V _O	\ldots 0 to \leq V _{CC}
Input Rise and Fall Slew Rate, dt/dv	0 to 10ns/V

Thermal Information

Thermal Resistance (Typical, Note 4) θ_{JA}	(^o C/W)
PDIP Package	75
SOIC Package	75
Maximum Junction Temperature	. 150 ⁰ C
Maximum Storage Temperature Range65°C t	o 150 ⁰ C
Maximum Lead Temperature (Soldering 10s)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

4. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Temperature Range 0°C to 70°C, V_{CC} Max = 5.25V, V_{CC} Min = 4.75V

					AMB	IENT TEM	PERATURI	E (T _A)	
		TEST CON	DITIONS		25	°C	0°C T	0 70 ⁰ C	
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	МАХ	MIN	MAX	
High Level Input Voltage	V _{IH}			4.75 to 5.25	2	-	2	-	V
Low Level Input Voltage	V _{IL}			4.75 to 5.25	-	0.8	-	0.8	V
High Level Output Voltage	V _{OH}	V _{IH} or V _{IL}	-15	Min	2.4	-	2.4	-	V
Low Level Output Voltage	V _{OL}	V _{IH} or V _{IL}	64	Min	-	0.55	-	0.55	V
High Level Input Current	Чн	V _{CC}		Max	-	0.1	-	1	μA
Low Level Input Current	Ι _{ΙL}	GND		Max	-	-0.1	-	-1	μA
Three-State Leakage Current	I _{OZH}	V _{CC}		Max	-	0.5	-	10	μA
	I _{OZL}	GND		Max	-	-0.5	-	-10	μA
Input Clamp Voltage	V _{IK}	V _{CC} or GND	-18	Min	-	-1.2	-	-1.2	V
Short Circuit Output Current (Note 5)	los	V _O = 0 V _{CC} or GND		Max	-60	-	-60	-	mA
Quiescent Supply Current, MSI	Icc	V _{CC} or GND	0	Max	-	8	-	80	μA
Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load	ΔI _{CC}	3.4V (Note 6)		Мах	-	1.6	-	1.6	mA

NOTES:

5. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.

6. Inputs that are not measured are at VCC or GND.

7. FCT Input Loading: All inputs are 1 unit load. Unit load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 1.6mA Max at 70°C.

			25 ⁰ C	0 ^о С ТО 70 ^о С			
PARAMETER	SYMBOL	V _{CC} (V)	ТҮР	MIN MAX		UNITS	
Propagation Delays							
Stored An $\rightarrow \overline{Bn}$	CD74FCT653	t _{PLH} , t _{PHL}	5	6.8	2	9	ns
Stored An \rightarrow Bn	CD74FCT654	t _{PLH} , t _{PHL}	5	6.8	2	9	ns
Stored $\overline{Bn} \to An$	CD74FCT653	t _{PZL}	5	6	2	8	ns
		t _{PLZ}	5	6.8	2	9	ns
Stored Bn \rightarrow An	CD74FCT654	t _{PZL} , t _{PLZ}	5	6.8	2	9	ns
$An \to \overline{Bn}$	CD74FCT653	t _{PLH} , t _{PHL}	5	6	2	8	ns
$An \to Bn$	CD74FCT654	t _{PLH} , t _{PHL}	5	6.8	2	9	ns
$\overline{Bn} \to An$	CD74FCT653	t _{PZL}	5	6	2	8	ns
		t _{PLZ}	5	6.8	2	9	ns
$Bn\toAn$	CD74FCT654	t _{PZL} , t _{PLZ}	5	6.8	2	9	ns
Select to Data (B Bus)	CD74FCT653, CD74FCT654	t _{PLH} , t _{PHL}	5	8.3	2	11	ns
Select to Data (A Bus)	CD74FCT653	t _{PZL}	5	6	2	8	ns
		t _{PLZ}	5	6.8	2	9	ns
Select to Data (A Bus)	CD74FCT654	t _{PZL} , t _{PLZ}	5	6.8	2	9	ns
Three-State Enabling Times (B Bus),	CD74FCT653	^t PZL ^{, t} PZH	5	10.5	2	14	ns
Bus to Output or Register to Output	CD74FCT654	^t PZL ^{, t} PZH	5	11.3	2	15	ns
Three-State Disabling Time (B Bus),	CD74FCT653	^t PLZ ^{, t} PZH	5	6.8	2	9	ns
Bus to Output or Register to Output	CD74FCT654	^t PLZ ^{, t} PZH	5	6.8	2	9	ns
Off State Enabling Times (A Bus),	CD74FCT653	t _{PZL}	5	10.5	2	14	ns
Bus to Output or Register to Output	CD74FCT654	t _{PZL}	5	11.3	2	15	ns
Off State Disabling Time (A Bus),	CD74FCT653	t _{PLZ}	5	6.8	2	9	ns
Bus to Output or Register to Output	CD74FCT654	t _{PLZ}	5	6.8	2	9	ns

Prerequisite for Switching t_r , t_f = 2.5ns, C_L = 50pF, R_L (Figures 3, 4)

			25 ⁰ C	0°C TO 70°C		
PARAMETER	SYMBOL	V _{CC} (V)	ТҮР	MIN	MAX	UNITS
Maximum Frequency (B Side as Outputs)	f _{MAX}	5 (Note 8)	-	80	-	MHz
Data to Clock Setup Time	ts∪	5	-	4	-	ns
Data to Clock Hold Time	tн	5	-	2	-	ns
Clock Pulse Width	t _W	5	-	6	-	ns

Switching t_r , $t_f = 2.5ns$, $C_L = 50pF$, R_L (Figures 3, 4)

			25 ⁰ C	0°C TO 70°C		
PARAMETER	SYMBOL	V _{CC} (V)	ТҮР	MIN	MAX	UNITS
Power Dissipation Capacitance	C _{PD}	-	-	-	-	pF
Min (Valley) V _{OH} (B Side) During Switching of Other Outputs (Output Under Test Not Switching)	V _{OHV} (Figure 1)	5	0.5	-	-	V
Max (Peak) V _{OL} During Switching of Other Outputs (Output Under Test Not Switching)	V _{OLP} (Figure 1)	5	1	-	-	V
Input Capacitance	Cl	-	-	-	10	pF
Three-State Output Capacitance (B Side)	CO	-	-	-	15	pF
Off-State Output Capacitance (A Side)	CO	-	-	-	15	pF

NOTES:

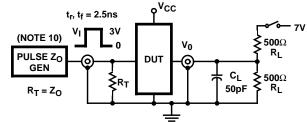
8. 5V: minimum is at 4.75V for 0° C to 70° C, typical is at 5V.

- 9. C_{PD}, measured per flip-flop, is used to determine the dynamic power consumption. PD
 - (per package) = $V_{CC} I_{CC} + \Sigma (V_{CC}^2 f_I C_{PD} + V_O^2 f_O C_L + V_{CC} \Delta I_{CC} D)$ where:

 V_{CC} = supply voltage

- ΔI_{CC} = flow through current x unit load
 - C_L = output load capacitance
 - \overline{D} = duty cycle of input high
 - f_{O} = output frequency
 - $f_I = input frequency$

Test Circuits and Waveforms



NOTE:

10. Pulse Generator for All Pulses: Rate \leq 1.0MHz; Z_{OUT} \leq 50\Omega; $t_{f},\,t_{r}$ \leq 2.5ns.

FIGURE 1. TEST CIRCUIT

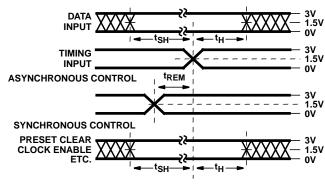


FIGURE 2. SETUP, HOLD, AND RELEASE TIMING

SWITCH POSITION

TEST	SWITCH			
t _{PLZ} , t _{PZL} , Open Drain	Closed			
^t PHZ, ^t PZH, ^t PLH, ^t PHL	Open			

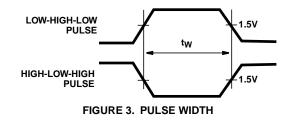
DEFINITIONS:

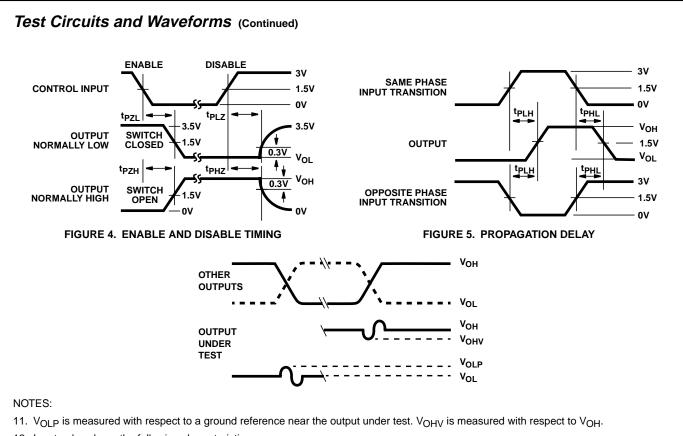
C_L = Load capacitance, includes jig and probe capacitance.

 R_T = Termination resistance, should be equal to Z_{OUT} of the Pulse Generator.

$$V_{IN} = 0V$$
 to 3V.

Input: $t_f = t_f = 2.5$ ns (10% to 90%), unless otherwise specified





- 12. Input pulses have the following characteristics: $P_{RR} \leq$ 1MHz, t_{r} = 2.5ns, t_{f} = 2.5ns, skew 1ns.
- 13. R.F. fixture with 700MHz design rules required. IC should be soldered into test board and bypassed with 0.1µF capacitor. Scope and probes require 700MHz bandwidth.

FIGURE 6. SIMULTANEOUS SWITCHING TRANSIENT WAVEFORMS

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